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APPLICATION FOR UNITED STATES PATENT **DECLARATION AND POWER OF ATTORNEY**

As a below named inventor, I declare that my residence, post office address and citizenship are as stated below next to my name; that I verily believe that I am the original, first and sole inventor if only one name is listed below, or an original, first and joint inventor if plural inventors are named below, of the subject matter which is claimed and for which a patent is sought on the invention entitled as set forth below, which is described in the attached specification; that I have reviewed and understand the contents of the specification, including the claims, as amended by any amendment specifically referred to in the oath or declaration; that no application for patent or inventor's certificate on this invention has been filed by me or my legal representatives or assigns in any country foreign to the United States of America; and that I acknowledge my duty to disclose information which is material to the patentability of this application in accordance with Title 37, Code of Federal Regulations, Section 1.56;

I further declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true, and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

TITLE OF INVENTION:

Method for Annealing Ultra-Thin, High Quality Gate Oxide Layers Using Oxidizer/Hydrogen Mixtures

POWER OF ATTORNEY: I HEREBY APPOINT PRACTITIONERS AT CUSTOMER NUMBER **23494** TO PROSECUTE THIS APPLICATION AND TRANSACT ALL BUSINESS IN THE PATENT AND TRADEMARK OFFICE CONNECTED THEREWITH

SEND CORRESPONDENCE TO:

Gary C. Honeycutt
 Texas Instruments Incorporated
 P.O. Box 655474, MS 3999
 Dallas, TX 75265

DIRECT TELEPHONE CALLS TO:

Gary C. Honeycutt
 (972) 238-7160

NAME OF INVENTOR: (1)

Hiroaki Niimi

NAME OF INVENTOR: (2)

Rajesh Khamankar

NAME OF INVENTOR: (3)

James J. Chambers

RESIDENCE & POST OFFICE ADDRESS:

430 Buckingham Road, Apt. #2136
 Richardson, Texas 75081

RESIDENCE & POST OFFICE ADDRESS:

715 Beal Lane
 Coppell, Texas 75019

RESIDENCE & POST OFFICE ADDRESS:

2501 Trailridge Drive
 Plano, Texas 75074

COUNTRY OF CITIZENSHIP:

Japan

COUNTRY OF CITIZENSHIP:

India

COUNTRY OF CITIZENSHIP:

United States

SIGNATURE OF INVENTOR:

SIGNATURE OF INVENTOR:

SIGNATURE OF INVENTOR:

DATE:

DATE:

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APPLICATION FOR UNITED STATES PATENT
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TITLE OF INVENTION: Method for Annealing Ultra-Thin, High Quality Gate Oxide Layers Using Oxidizer/Hydrogen Mixtures		
NAME OF INVENTOR: (4) Sunil Hattangady	NAME OF INVENTOR: (5) Antonio L.P. Rotondaro	NAME OF INVENTOR: (6) N/A
RESIDENCE & POST OFFICE ADDRESS: 2403 St. Remy Drive McKinney, Texas 75070	RESIDENCE & POST OFFICE ADDRESS: 7715 Willow Vine Court, Apt. 223 Dallas, Texas 75230	RESIDENCE & POST OFFICE ADDRESS:
COUNTRY OF CITIZENSHIP: India	COUNTRY OF CITIZENSHIP: Brazil	COUNTRY OF CITIZENSHIP:
SIGNATURE OF INVENTOR:	SIGNATURE OF INVENTOR:	SIGNATURE OF INVENTOR:
DATE:	DATE:	DATE: